

1.0 SCOPE

This specification documents the detailed requirements for Analog Devices space qualified die including die qualification as described for Class K in MIL-PRF-38534, Appendix C, Table C-II except as modified herein.

The manufacturing flow described in the STANDARD DIE PRODUCTS PROGRAM brochure at http://www.analog.com/marketSolutions/militaryAerospace/pdf/Die_Broc.pdf is to be considered a part of this specification.

This data sheet specifically details the space grade version of this product. A more detailed operational description and a complete data sheet for commercial product grades can be found at www.analog.com/AD574

2.0 Part Number. The complete part number(s) of this specification follow:

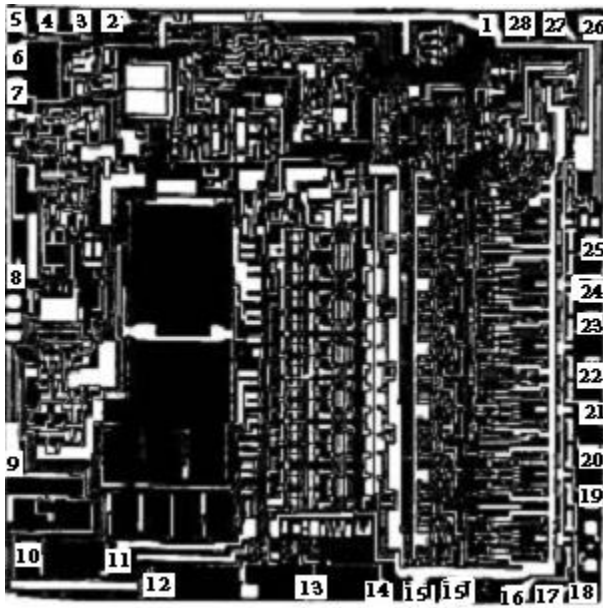
Part Number	Description
AD574-000C	12-Bit-ADC with Microprocessor Interface
AD574R000C	Radiation Tested 12-Bit-ADC with Microprocessor Interface

3.0 Die Information

3.1 Die Dimensions

Die Size	Die Thickness	Bond Pad Metalization
179 x 180	19 mil ± 2 mil	Al/Cu

3.2 Die Picture



1 V_{LOGIC}	28 STATUS
2 $12/8$	27 DB11
3 $\overline{\text{CS}}$	26 DB10
4 A_0	25 DB9
5 $R/\overline{\text{C}}$	24 DB8
6 CE	23 DB7
7 V_{CC}	22 DB6
8 REF_{OUT}	21 DB5
9 AC	20 DB4
10 REF_{IN}	19 DB3
11 V_{EE}	18 DB2
12 BIP OFF	17 DB1
13 $10V_{\text{IN}}$	16 DB0
14 $20V_{\text{IN}}$	15 DC

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Rev. J

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3.3 Absolute Maximum Ratings

V_{CC} to Digital Common.....	0 to +16.5V dc
V_{EE} to Digital Common.....	0 to -16.5V dc
V_{LOG} to Digital Common.....	0 to +7V dc
Analog to Digital Common.....	$\pm 1V$ dc
Control Inputs (\overline{CE} , \overline{CS} , A_0 , 12/8, R/ \overline{C}) to Digital Common.....	-0.5V dc to $V_{LOG}+0.5V$ dc
Analog Inputs (REF IN, BIP OFF, 10 V_{IN}) to Analog Common.....	V_{EE} to V_{CC}
20 V_{IN} Analog Input Voltage to Analog Common	$\pm 24V$ dc
$V_{REF OUT}$	Indefinite short to common, 10mS
.....	short to V_{CC}
Storage Temperature	-65°C to +150°C
Junction Temperature (T_J).....	+175°C
Operating Temperature Range.....	-55°C to +125°C

4.0 Die Qualification

In accordance with class-K version of MIL-PRF-38534, Appendix C, Table C-II, except as modified herein.

- (a) Qual Sample Size and Qual Acceptance Criteria – 10/0
- (b) Qual Sample Package – Ceramic DIP
- (c) Pre-screen electrical test over temperature performed post-assembly prior to die qualification.

Table I-Dice Electrical Characteristics

Parameter	Symbol	Conditions 1/	Limit Min	Limit Max	Units
Power Supply Current From V_{LOG}	I_{LOG}			40	mA
Power Supply Current From V_{CC}	I_{CC}			5	mA
Power Supply Current From V_{EE}	I_{EE}		-30		mA
Resolution			12		Bits
Integral Linearity Error Differential Linearity Error (Minimum Resolution For Which No Missing Codes Guaranteed)	ILE DLE		-0.5	0.5	LSB
			12		Bits
Unipolar Offset Voltage Error	V_{IO}		-2.0	2.0	LSB

Table I – Dice Electrical Characteristics (Continued)

Parameter	Symbol	Conditions 1/	Limit Min	Limit Max	Units
Bipolar Offset Voltage Error	B _Z		-4.0	4.0	LSB
Gain Error	ΔA _E	With 50Ω resistor from REF OUT to REF IN		.25	% of F.S.
Power Supply Sensitivity (Maximum Change In Full Scale Calibration)	+P _{SS1}	+13.5V ≤ V _{CC} ≤ +16.5V	-1.0	1.0	LSB
	+P _{SS2}	+11.4V ≤ V _{CC} ≤ +12.6V			
	+P _{SS3}	+4.5V ≤ V _{LOG} ≤ + 5.5V	-0.5	0.5	
	-P _{SS1}	-16.5V ≤ V _{EE} ≤ -13.5V	-1.0	1.0	
	-P _{SS2}	-12.6V ≤ V _{EE} ≤ -11.4V			
Input Impedance	Z _{IN}	10V span	3	7	kΩ
		20V span	6	14	
Internal Reference Voltage	V _{REF}	2/	9.98	10.02	V
Input Voltage (CE, \overline{CS} , 12/8, R/ \overline{C} , A ₀) 3/	V _{IH}	Logic "1"	2.0	5.5	V
	V _{IL}	Logic "0"	-0.5	0.8	
Input Current	I _{IN}		-20	+20	μA
Output Voltage (DB11-DB0, STS)	V _{OL}	Logic "0", I _{SINK} = +1.6mA		400	mV
Output Voltage (DB11-DB0)	V _{OH}	Logic "1", I _{SOURCE} = +500μA	2.4		V
High Impedance State Output Current	I _Z	High-Z state, DB11 – DB0 only	-20	+20	μA

Table I Notes:

- 1/ V_{CC} = ±15V, V_{LOG} = +5V, V_{EE} = -15V, T_A = 25°C, unless otherwise specified.
2/ The reference voltage external load current shall be a constant dc and shall not exceed 1.5 mA. Reference should be buffered for operation of ±12V supplies. External load should not change during conversion.
3/ 12/8 is not TTL compatible and must be hard wired to V_{LOG} or digital ground.

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Table II - Electrical Characteristics for Qual Samples

Parameter	Symbol	Conditions 1/	Sub-groups	Limit Min	Limit Max	Units
Power Supply Current From V_{LOG}	I_{LOG}		1, 2, 3		40	mA
		M, D, L, R 5/	1		40	
Power Supply Current From V_{CC}	I_{CC}		1, 2, 3		5	
		M, D, L, R 5/	1		5	
Power Supply Current From V_{EE}	I_{EE}		1, 2, 3	-30		
		M, D, L, R 5/	1	-30		
Integral Linearity Error	ILE		1	-0.5	0.5	LSB
			2, 3	-1.0	1.0	
		M, D, L, R 5/	1	-1.0	1.0	
Differential Linearity Error (Minimum Resolution For Which No Missing Codes Guaranteed) 6/	DLE		1	12		Bits
			2, 3	12		
Unipolar Offset Voltage Error	V_{IO}	Using internal reference	1	-2.0	2.0	LSB
		M, D, L, R 5/	1	-3.0	3.0	
Unipolar Offset Drift 6/	$\frac{\Delta V_{IO}}{\Delta T}$	Using internal reference	2, 3	-1.0	1.0	
Bipolar Offset Voltage Error	B_Z	Using internal reference	1	-4.0	4.0	
		M, D, L, R 5/	1	-5.0	5.0	
Bipolar Zero Offset Drift 6/	$\frac{\Delta B_Z}{T}$	Using internal reference	2, 3	-2.0	+2.0	
Gain Error	ΔA_E	With 50 Ω resistor from REF OUT to REF IN	1		.25	% of F.S.
		M, D, L, R 5/	1		.35	
Gain Error Drift 6/	$\frac{\Delta A_E}{\Delta T}$	Using internal reference	2, 3	-25.0	25.0	ppm/°C
Power Supply Sensitivity (Maximum Change In Full Scale Calibration) 6/	+P _{SS1}	+13.5V \leq V _{CC} \leq +16.5V	1	-1.0	1.0	LSB
	+P _{SS2}	+11.4V \leq V _{CC} \leq +12.6V				
	+P _{SS3}	+4.5V \leq V _{LOG} \leq +5.5V	1	-0.5	0.5	
	-P _{SS1}	-16.5V \leq V _{EE} \leq -13.5V	1	-1.0	1.0	
	-P _{SS2}	-12.6V \leq V _{EE} \leq -11.4V				
Input Impedance 6/	Z_{IN}	10V span	1	3	7	k Ω
		20V span	1	6	14	

Table II - Electrical Characteristics for Qual Samples

Parameter	Symbol	Conditions 1/	Sub- groups	Limit Min	Limit Max	Units
Output Voltage (DB11-DB0, STS) 6/	V_{OL}	Logic "0", $T_A = +25^\circ\text{C}$, $I_{SINK} = +1.6\text{mA}$	1, 2, 3		400	mV
Output Voltage (DB11-DB0) 6/	V_{OH}	Logic "1", $T_A = +25^\circ\text{C}$, $I_{SOURCE} = +500\mu\text{A}$	1	2.4		V
High Impedance State Output Current 6/	I_Z	High-Z state, $T_A = +25^\circ\text{C}$, DB11-DB0 only	1	-20	+20	μA
Low R/\bar{C} Pulse Width 4/ 6/	t_{HRL}		9	250		ns
STS Delay from R/\bar{C} 4/ 6/	t_{DS}		9		600	ns
Data Valid After R/\bar{C} Low 4/ 6/	t_{HDR}		9		25	ns
STS Delay After Valid Data 4/ 6/	t_{HS}		9	300	1000	ns
High R/\bar{C} Pulse Width 6/	t_{HRH}		9	300		ns
Data Access Time 6/	t_{DDR}		9		250	ns
STS Delay from CE 6/	t_{DSC}		9		350	ns
CE Pulse Width 6/	t_{HEC}		9	300		ns
Conversion Time 6/	t_C	8-bit cycle	9	10	24	μs
		12-bit cycle	9	15	35	
Access Time (from CE) 6/	t_{DD}		9		200	ns

Table II Notes:

- 1/ $V_{CC} = \pm 15\text{V}$, $V_{LOG} = +5\text{V}$, $V_{EE} = -15\text{V}$, $-55^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$, unless otherwise specified.
- 2/ The reference voltage external load current shall be a constant dc and shall not exceed 1.5 mA. Reference should be buffered for operation of $\pm 12\text{V}$ supplies. External load should not change during conversion.
- 3/ 12/8 is not TTL compatible and must be hard wired to V_{LOG} or digital ground.
- 4/ Subgroups 10 and 11, if not tested, shall be guaranteed to the specified limits.
- 5/ Tested at 100Krad
- 6/ Not Tested Post Irradiation.

Table III - Delta Parameter Table

Parameter	Symbol	Sub-groups	Post Burn In Limit		Post Life Test Limit		Life Test Delta	Units
			Min	Max	Min	Max		
Unipolar Offset Voltage Error	Uni V_{IO}	1	-2.0	2.0	-2.5	2.5	± 0.5	LSB
Bipolar Offset Voltage Error	Bpze	1	-4.0	4.0	-5.0	5.0	± 1.0	LSB
Gain Error	A_E	1	-0.25	0.25	-0.25	0.35	$\pm .10$	%FSR

5.0 Life Test/Burn-In Information

- 5.1 HTRB is not applicable for this drawing.
- 5.2 Burn-in is per MIL-STD-883 Method 1015 test condition B or C.
- 5.3 Steady state life test is per MIL-STD-883 Method 1005.

Rev	Description of Change	Date
A	Initiate	04-Oct-2001
B	Update web address	Jan. 25, 2002
C	Update web address. Add Radiation limits and part number.	4-Mar-03
D	Update 1.0 Scope description.	2 Aug. 2007
E	Update header/footer & add to 1.0 Scope description.	Feb. 14, 2008
F	Remove reference to condition 5/ note on Table I & add Junction Temperature (T_J).... +175°C & Operating Temperature Range....-55°C to +125°C to Section 3.3-Absolute Max. Ratings	March 27, 2008
G	Updated Section 4.0c note to indicate pre-screen temp testing being performed.	6-JUN-2009
H	Updated Font and Font Size to Standardize to ADI format	20-Sep-2011
I	Correct typo from mA to mV in output voltage of table II	17-MAR-2014
J	Append S to Aerospace Generic Title	21-Mar-2014